

L Number	Hits	Search Text	DB	Time stamp
1	9	@ad<=20021029 and 'polysilicon plug' with 'conductive barrier'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/28 09:06
2	95	@ad<=20021029 and 'trench capacitor' and 'polysilicon plug' and 'barrier'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/28 09:07
3	50	@ad<=20021029 and 'stack capacitor' and 'polysilicon plug' and 'barrier'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/28 09:07
4	1		USPAT	2004/10/28 09:17
5	1		USPAT	2004/10/28 09:28
6	1		USPAT	2004/10/28 09:36
7	1		USPAT	2004/10/28 09:36
8	1		USPAT	2004/10/28 09:36
9	1		USPAT	2004/10/28 09:36
10	1		USPAT	2004/10/28 09:37
-	2	"20040080051"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 12:08
-	551	@ad<=20021029 and (257/300).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 12:14
-	1372	@ad<=20021029 and (257/301-302).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 12:15
-	1017	@ad<=20021029 and (257/303-304).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 12:15
-	1997	@ad<=20021029 and (257/305-306).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 12:16
-	494	@ad<=20021029 and (257/307-308).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 12:17
-	1338	@ad<=20021029 and (257/309-310).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 12:17
-	534	@ad<=20021029 and (257/311-313).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 12:18

-	137	@ad<=20021029 and (257/906).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 12:18
-	96	@ad<=20021029 and (257/908).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 12:19
-	2732	@ad<=20021029 and (257/296).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 14:59
-	183	@ad<=20021029 and 'DRAM' and 'Micron' and 'transistor' and 'conductive barrier'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 12:48
-	4	@ad<=20021029 and 'DRAM' same 'plug' with 'conductive barrier'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 14:14
-	306	@ad<=20021029 and 'DRAM' same 'plug' same 'barrier'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 12:51
-	23	@ad<=20021029 and 'DRAM' and 'conductive plug' with 'conductive barrier'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 14:05
-	2	("6531730").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 13:25
-	1	"6071770".PN.	USPAT	2004/10/27 13:26
-	1	"6066528".PN.	USPAT	2004/10/27 13:26
-	1	"5973344".PN.	USPAT	2004/10/27 13:27
-	1	"5796136".PN.	USPAT	2004/10/27 13:27
-	1	"5796136".PN.	USPAT	2004/10/27 13:28
-	1	"5631804".PN.	USPAT	2004/10/27 13:28
-	1	"5506166".PN.	USPAT	2004/10/27 13:28
-	1	"5489548".PN.	USPAT	2004/10/27 13:28
-	1	"5471364".PN.	USPAT	2004/10/27 13:29
-	1	"5401680".PN.	USPAT	2004/10/27 13:30
-	1	"5396094".PN.	USPAT	2004/10/27 13:30
-	324	@ad<=20021029 and 'polysilicon plug' with 'barrier'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/28 09:05
-	92	@ad<=20021029 and 'polysilicon plug' with 'diffusion barrier'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 14:15

-	70	@ad<=20021029 and 'polysilicon plug' with 'barrier metal'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 14:14
-	61	@ad<=20021029 and 'DRAM' same 'plug' with 'Titanium nitride'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 15:19
-	81	@ad<=20021029 and 'polysilicon plug' with 'titanium nitride'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 14:15
-	978	@ad<=20021029 and (438/240).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 15:00
-	2	("6580112").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 15:21
-	2	("6486529").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 15:24
-	1	"6348391".PN.	USPAT	2004/10/27 15:23
-	2	"20010050390"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 15:27
-	2	("6635561").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 15:27